TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MET374AFK

Octal D-Type Flip-Flop with 3-State Output

The TC7MET374AFK is an advanced high speed CMOS octal flip-flop with 3-state output fabricated with silicon gate $\rm C^2MOS$ technology.

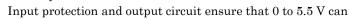
It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type flip-flop is controlled by a clock input (CK) and a output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The input voltage are compatible with TTL output voltage.

This device may be used as a level converter for interfacing $3.3\ V$ to $5\ V$ system.



be applied to the input and output (Note) pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

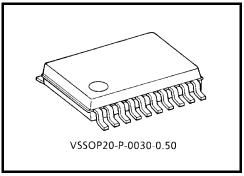




- High speed: $f_{max} = 140 \text{ MHz (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- Compatible with TTL outputs: $V_{IL} = 0.8 \text{ V (max)}$

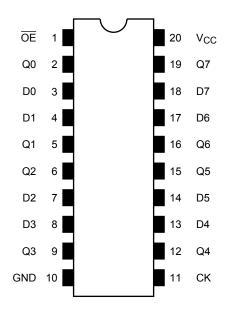
$$V_{IH} = 2.0 \text{ V (min)}$$

- Power down protection is provided on all inputs and outputs.
- $\bullet \quad \text{Balanced propagation delays: } t_{pLH} \approx t_{pHL}$
- Low noise: VOLP = 1.5 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 374 type.

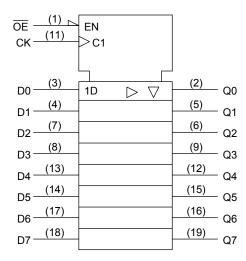


Weight: 0.03 g (typ.)

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

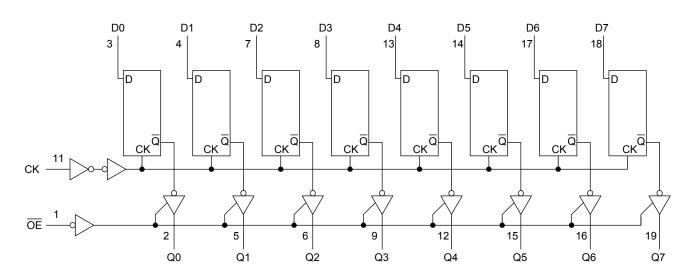
	Outputs		
ŌĒ	CK	D	Outputs
Н	Х	Х	Z
L	\neg	Х	Qn
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q_n: No change

System Diagram





Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	Vout	−0.5~7.0 (Note 2)	V
DC output voltage	VOU1	-0.5~V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20 (Note 4)	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Output in off-state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~5.5 (Note 2)	V
Output voitage		0~V _{CC} (Note 3)	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~20	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

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Note 2: Output in off-state

Note 3: High or low state

Electrical Characteristics

DC Characteristics

Characteristics		Cumbal	Symbol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
		Syllibol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
Input voltage	High level	V _{IH}		_	4.5~5.5	2.0	_	_	2.0	_	V
input voitage	Low level	V _{IL}		_	4.5~5.5	_	_	0.8	_	0.8	V
	I Bada I a		V _{IN} = V _{IH}	I _{OH} = -50 μA	4.5	4.4	4.5	_	4.4	_	
Output voltage Low level	nigii ievei	V _{OH}	or V _{IL}	I _{OH} = -8 mA	4.5	3.94	_	_	3.80	_	V
	Lowlovel	Va	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 50 \mu A$	4.5	_	0	0.1	_	0.1	
	Low level	V _{OL}		I _{OL} = 8 mA	4.5	_	_	0.36	_	0.44	
3-state output of	f-state current	loz	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		5.5	_	_	±0.25	_	±2.50	μА
Input leakage cu	ırrent	I _{IN}	V _{IN} = 5.5	V or GND	0~5.5	_	_	±0.1	_	±1.0	μΑ
Icc		V _{IN} = V _{CC} or GND		5.5	_	_	4.0	_	40.0	μА	
Quiescent supply current		I _{CCT}	Per input: V _{IN} = 3.4 V Other input: V _{CC} or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage	current	I _{OPD}	V _{OUT} = 5.5 V		0	_	_	0.5	_	5.0	μА

Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = -40~85°C	Unit
Characteristics Symbol Test Condition		rest Condition	V _{CC} (V)	Тур.	Limit	Limit	Offic
Minimum pulse width (CK)	t _{w (H)} t _{w (L)}	_	5.0 ± 0.5	_	6.5	8.5	ns
Minimum set-up time	ts	_	5.0 ± 0.5	_	2.5	2.5	ns
Minimum hold time	t _h		5.0 ± 0.5	_	2.5	2.5	ns

AC Electrical Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -4	Unit	
Characteristics	Syllibol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Oi ii
Propagation delay time	t _{pLH}	_	5.0 ± 0.5	15	_	4.1	9.4	1.0	10.5	ns
(CK-Q)	tpHL	_	3.0 ± 0.5	50		5.6	10.4	1.0	11.5	10
3-state output enable time	t _{pZL}	$R_L = 1 k\Omega$	5.0 ± 0.5	15		6.5	10.2	1.0	11.5	ns
5-state output enable time	t _{pZH}		3.0 ± 0.3	50		7.3	11.2	1.0	12.5	115
3-state output disable time	t _{pLZ}	$ \begin{array}{c c} t_{pLZ} \\ t_{pHZ} \\ f_{max} \end{array} \hspace{0.5cm} R_L = 1 \ k\Omega $	5.0 ± 0.5	15		7.0	11.2	1.0	12.0	
	·			50	90	140	١	80	١	ns
Maximum clock frequency	f _{max}	_	5.0 ± 0.5	50	85	130		75		MHz
Output to output skew	t _{osLH} t _{osHL}	(Note 1)	5.0 ± 0.5	50		_	1.0	_	1.0	ns
Input capacitance	C _{IN}	_			4	10	_	10	pF	
Output capacitance	C _{OUT}	_			9		_		pF	
Power dissipation capacitance	C _{PD}	(Note 2)		_	25	_	_	_	pF	

Note 1: Parameter guaranteed by design.

 $t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$

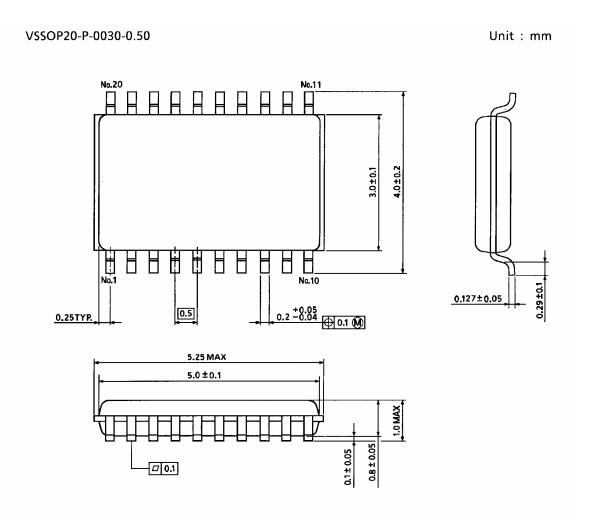
And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

 C_{PD} (total) = 14 + 11 · n

Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Ta = 25°C		25°C	Unit
Characteristics	Syllibol	Test Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	1.1	1.5	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-1.1	-1.5	V
Minimum high level dynamic input voltage V_{IH}	V _{IHD}	C _L = 50 pF	5.0	_	2.0	V
Maximum low level dynamic input voltage V _{IL}		C _L = 50 pF	5.0	_	0.8	V

Package Dimensions



Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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